

74AUP2G34

Low-power dual buffer

Rev. 5 — 10 January 2013

Product data sheet

1. General description

The 74AUP2G34 provides two low-power, low-voltage buffers.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} .

The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information

Type number	Package				Version
	Temperature range	Name	Description		
74AUP2G34GW	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads		SOT363
74AUP2G34GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm		SOT886
74AUP2G34GF	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm		SOT891
74AUP2G34GN	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm		SOT1115
74AUP2G34GS	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm		SOT1202

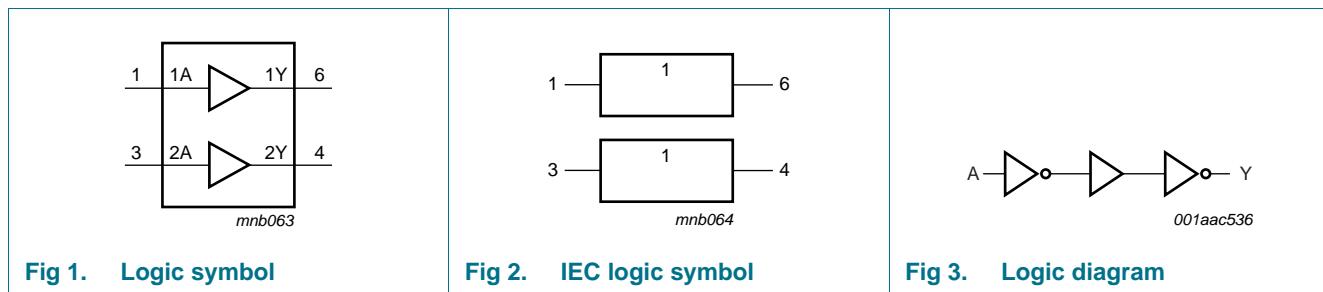
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AUP2G34GW	aA
74AUP2G34GM	aA
74AUP2G34GF	aA
74AUP2G34GN	aA
74AUP2G34GS	aA

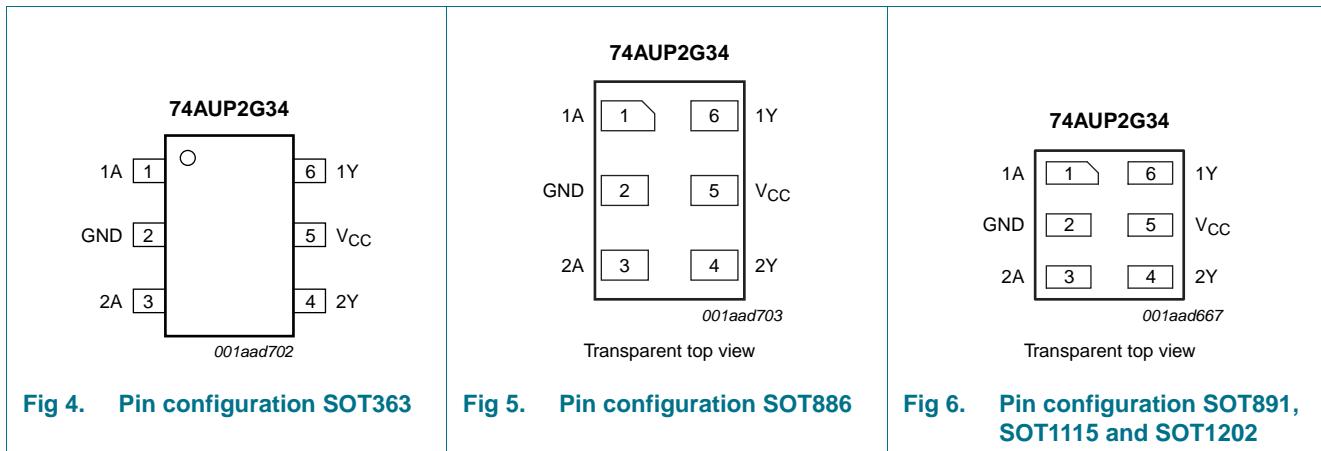
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V _{CC}	5	supply voltage
1Y	6	data output

7. Functional description

Table 4. Function table^[1]

Input	Output
nA	nY
L	L
H	H

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V _I	input voltage		[1] -0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
V _O	output voltage	Active mode and Power-down mode	[1] -0.5	+4.6	V
I _O	output current	V _O = 0 V to V _{CC}	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{STG}	storage temperature		-65	+150	°C
P _{TOT}	total power dissipation	T _{amb} = -40 °C to +125 °C	[2] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 °C the value of P_{TOT} derates linearly with 4.0 mW/K.

For XSON6 packages: above 118 °C the value of P_{TOT} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
V _I	input voltage		0	3.6	V
V _O	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{AMB}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	-	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V	V _{CC} – 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	μA
	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.2	μA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.2	μA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	-	-	40	μA
C _I	input capacitance	V _{CC} = 0 V to 3.6 V; V _I = GND or V _{CC}	-	0.8	-	pF
C _O	output capacitance	V _O = GND; V _{CC} = 0 V	-	1.7	-	pF

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.7 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.97	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.85	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.67	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.55	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.5	μA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.5	μA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.6	μA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.9	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	-	-	50	μA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.75 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.6 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.77	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.67	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.40	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.30	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.75	μA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.75	μA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.75	μA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	1.4	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	-	-	75	μA

11. Dynamic characteristics

Table 8. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 5 pF									
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]						
		V _{CC} = 0.8 V	-	14.9	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.6	4.7	9.2	2.0	10.0	11.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.1	3.4	5.7	1.6	6.5	7.2	ns
		V _{CC} = 1.65 V to 1.95 V	1.8	2.9	4.5	1.4	5.2	5.8	ns
		V _{CC} = 2.3 V to 2.7 V	1.5	2.3	3.5	1.2	4.2	4.6	ns
		V _{CC} = 3.0 V to 3.6 V	1.4	2.1	3.2	1.0	3.8	4.2	ns
C_L = 10 pF									
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]						
		V _{CC} = 0.8 V	-	18.4	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.2	5.6	10.9	2.3	11.8	13.1	ns
		V _{CC} = 1.4 V to 1.6 V	2.6	4.1	6.7	1.9	7.7	8.5	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	3.4	5.3	1.7	6.2	6.9	ns
		V _{CC} = 2.3 V to 2.7 V	2.0	2.9	4.2	1.5	5.0	5.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.7	2.6	3.8	1.4	4.6	5.1	ns
C_L = 15 pF									
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]						
		V _{CC} = 0.8 V	-	21.9	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	6.4	12.6	2.6	13.8	15.2	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	4.6	7.6	2.2	8.9	9.8	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	3.9	6.0	2.0	7.2	7.9	ns
		V _{CC} = 2.3 V to 2.7 V	2.3	3.3	4.8	1.8	5.7	6.3	ns
		V _{CC} = 3.0 V to 3.6 V	2.1	3.1	4.2	1.6	5.0	5.5	ns
C_L = 30 pF									
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]						
		V _{CC} = 0.8 V	-	32.1	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.8	8.7	16.3	3.6	18.9	20.8	ns
		V _{CC} = 1.4 V to 1.6 V	4.0	6.2	10.3	3.4	12.2	13.4	ns
		V _{CC} = 1.65 V to 1.95 V	3.6	5.2	8.1	3.2	9.8	10.8	ns
		V _{CC} = 2.3 V to 2.7 V	3.0	4.4	6.4	2.7	7.7	8.5	ns
		V _{CC} = 3.0 V to 3.6 V	2.9	4.2	5.6	2.5	6.5	7.2	ns

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 5 pF, 10 pF, 15 pF and 30 pF									
C _{PD}	power dissipation capacitance	f _i = 1 MHz; V _I = GND to V _{CC} [3][4]							
		V _{CC} = 0.8 V	-	2.5	-	-	-	-	pF
		V _{CC} = 1.1 V to 1.3 V	-	2.6	-	-	-	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	2.7	-	-	-	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	2.9	-	-	-	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	3.4	-	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	4.0	-	-	-	-	pF

[1] All typical values are measured at nominal V_{CC}.[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] All specified values are the average typical values over all stated loads.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

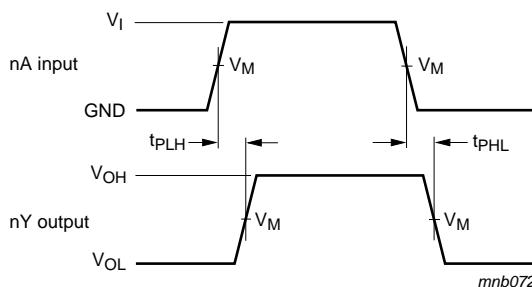
$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;f_o = output frequency in MHz;C_L = load capacitance in pF;V_{CC} = supply voltage in V;

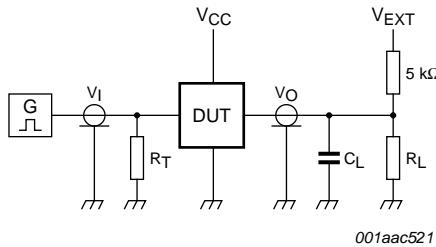
N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

Measurement points are given in [Table 9](#).Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.**Fig 7. The data input (nA) to output (nY) propagation delays****Table 9. Measurement points**

Supply voltage	Output	Input		
V _{CC} 0.8 V to 3.6 V	V _M 0.5 × V _{CC}	V _M 0.5 × V _{CC}	V _I V _{CC}	t _r = t _f ≤ 3.0 ns



Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 8. Test circuit for measuring switching times

Table 10. Test data

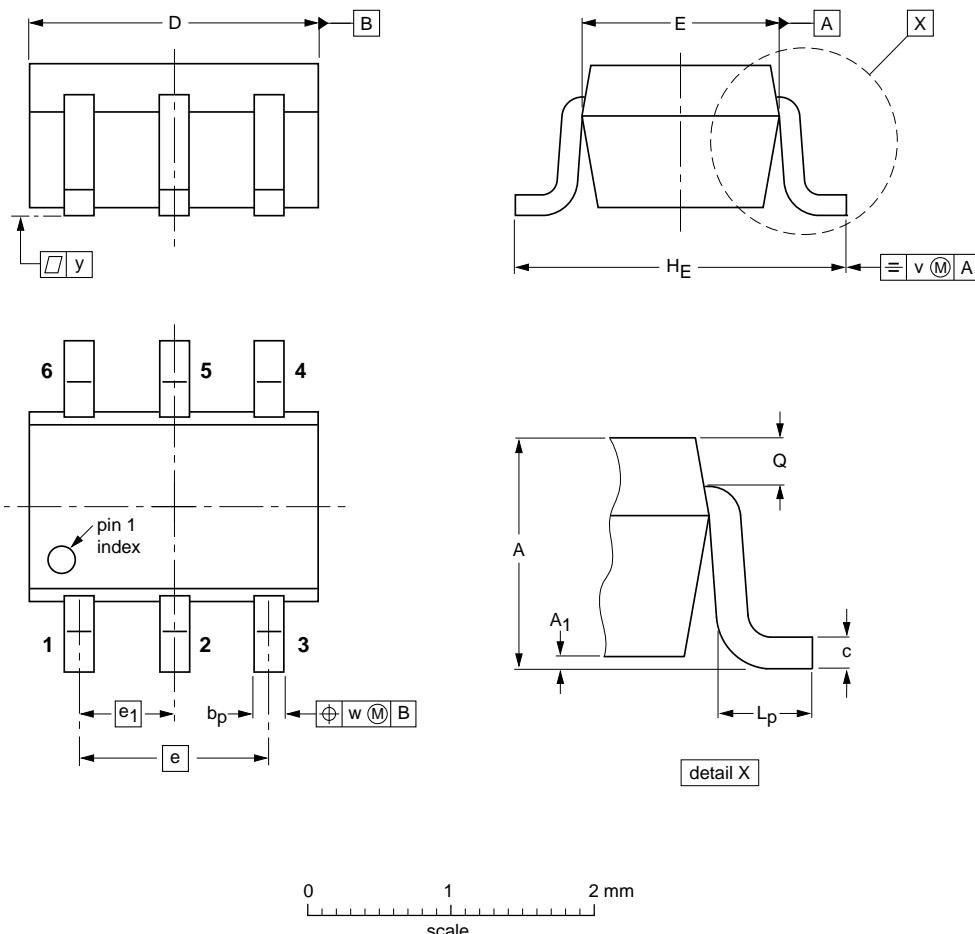
Supply voltage	Load	V_{EXT}			
V_{CC}	C_L	R_L ^[1]	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	2 $\times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 \text{ k}\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 \text{ M}\Omega$.

13. Package outline

Plastic surface-mounted package; 6 leads

SOT363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			-04-11-08- 06-03-16

Fig 9. Package outline SOT363 (SC-88)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1.45 \times 0.5$ mm

SOT886

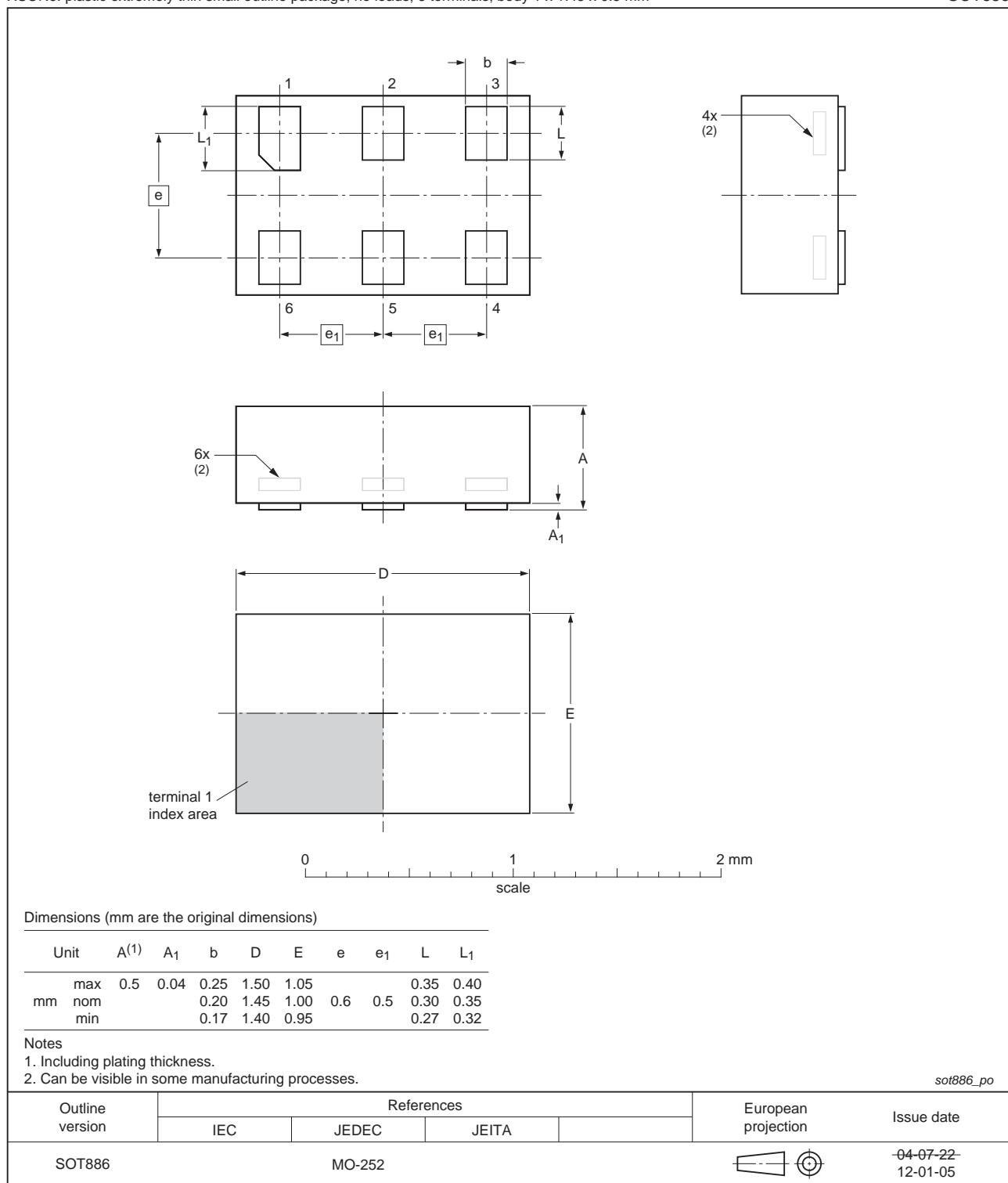
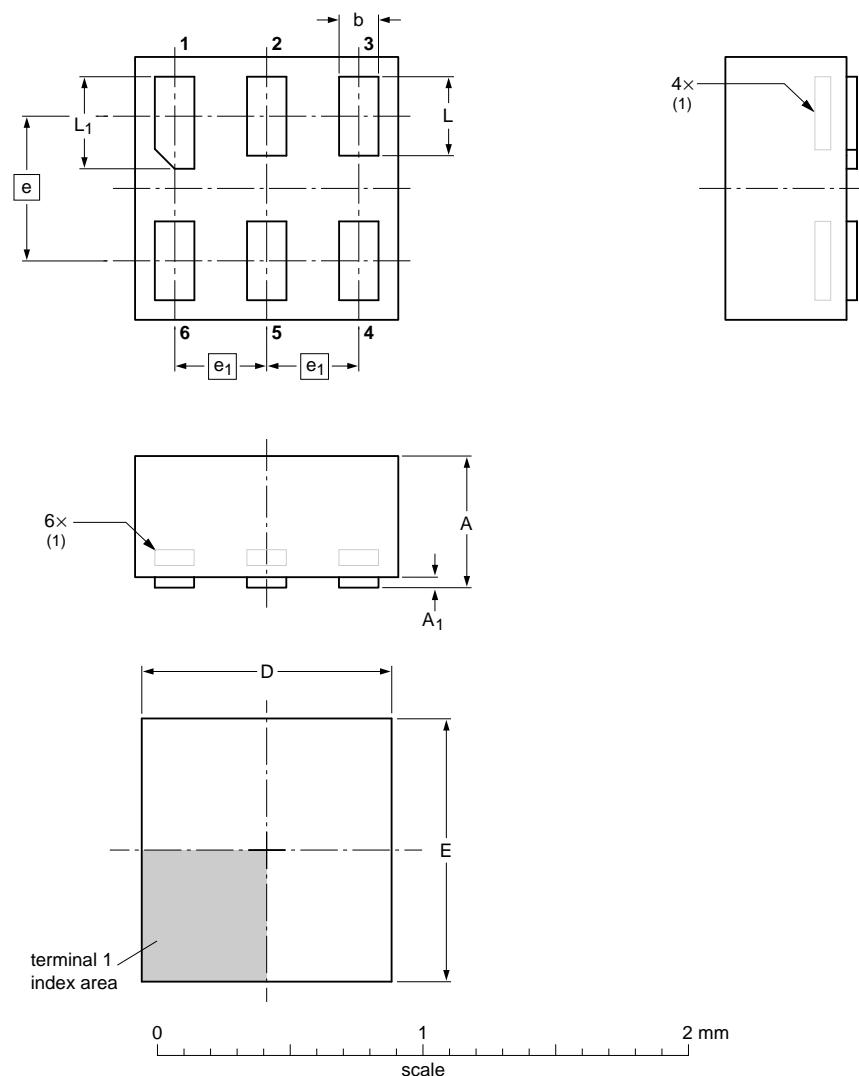


Fig 10. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

**DIMENSIONS (mm are the original dimensions)**

UNIT	A max	A ₁ max	b	D	E	e	e ₁	L	L ₁
mm	0.5	0.04	0.20 0.12	1.05 0.95	1.05 0.95	0.55	0.35	0.35 0.27	0.40 0.32

Note

1. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT891						05-04-06 07-05-15

Fig 11. Package outline SOT891 (XSON6)

**XSON6: extremely thin small outline package; no leads;
6 terminals; body 0.9 x 1.0 x 0.35 mm**

SOT1115

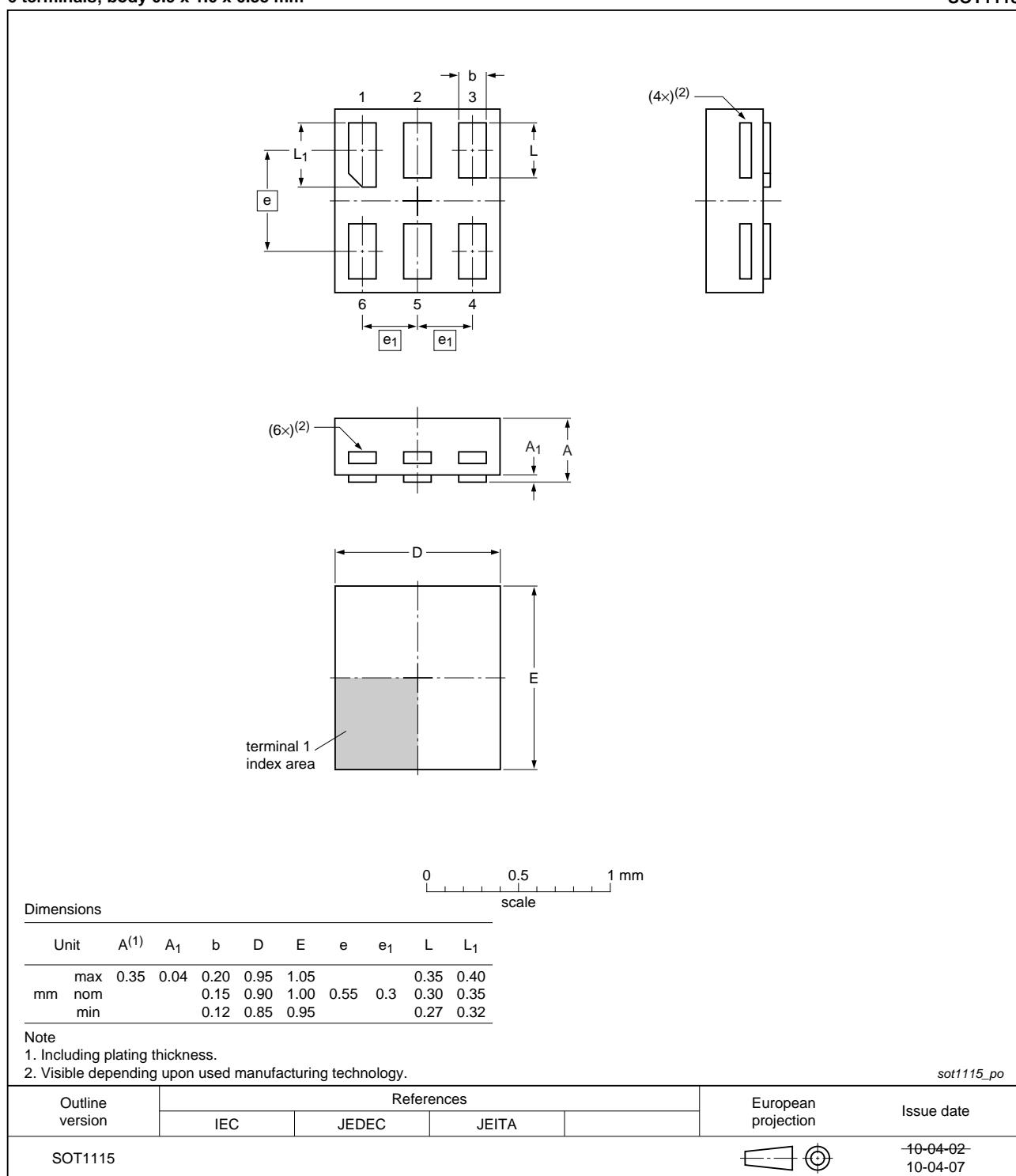


Fig 12. Package outline SOT1115 (XSON6)

**XSON6: extremely thin small outline package; no leads;
6 terminals; body 1.0 x 1.0 x 0.35 mm**

SOT1202

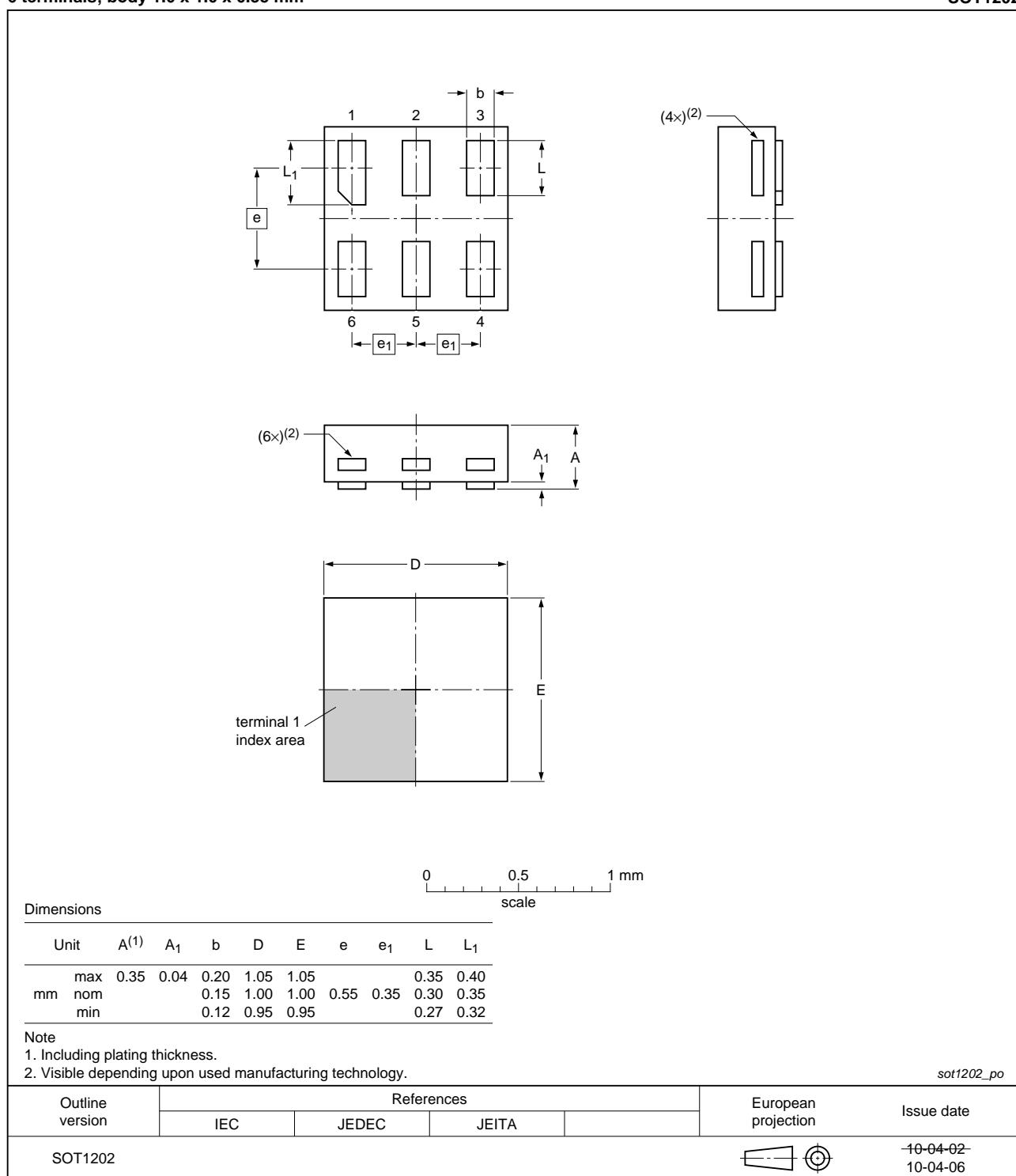


Fig 13. Package outline SOT1202 (XSON6)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G34 v.5	20130110	Product data sheet	-	74AUP2G34 v.4
Modifications:		• Package outline drawing of SOT886 (Figure 10) modified.		
74AUP2G34 v.4	20111206	Product data sheet	-	74AUP2G34 v.3
Modifications:		• Legal pages updated.		
74AUP2G34 v.3	20100903	Product data sheet	-	74AUP2G34 v.2
74AUP2G34 v.2	20080131	Product data sheet	-	74AUP2G34 v.1
74AUP2G34 v.1	20061122	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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18. Contents

1	General description	1
2	Features and benefits	1
3	Ordering information	2
4	Marking	2
5	Functional diagram	2
6	Pinning information	3
6.1	Pinning	3
6.2	Pin description	3
7	Functional description	3
8	Limiting values	4
9	Recommended operating conditions	4
10	Static characteristics	5
11	Dynamic characteristics	8
12	Waveforms	9
13	Package outline	11
14	Abbreviations	16
15	Revision history	16
16	Legal information	17
16.1	Data sheet status	17
16.2	Definitions.....	17
16.3	Disclaimers.....	17
16.4	Trademarks.....	18
17	Contact information	18
18	Contents	19

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